

HiPerFRED

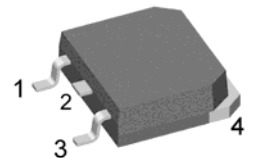
$$\begin{aligned} V_{RRM} &= 600 \text{ V} \\ I_{FAV} &= 60 \text{ A} \\ t_{rr} &= 35 \text{ ns} \end{aligned}$$

High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Single Diode

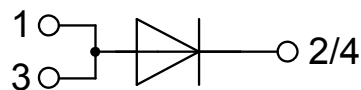
Part number

DSEP60-06AT

Marking on Product: DSEP60-06AT



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-268AA (D3Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

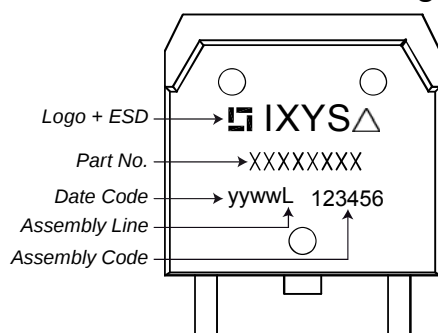
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Fast Diode				Ratings				
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse blocking voltage	T _{VJ} = 25°C				600	V	
V _{RRM}	max. repetitive reverse blocking voltage	T _{VJ} = 25°C				600	V	
I _R	reverse current, drain current	V _R = 600 V	T _{VJ} = 25°C			650	μA	
		V _R = 600 V	T _{VJ} = 150°C			2,5	mA	
V _F	forward voltage drop	I _F = 60 A	T _{VJ} = 25°C			2,04	V	
		I _F = 120 A				2,33	V	
		I _F = 60 A	T _{VJ} = 150°C			1,39	V	
		I _F = 120 A				1,70	V	
I _{FAV}	average forward current	T _C = 130°C rectangular d = 0.5	T _{VJ} = 175°C			60	A	
V _{F0}	threshold voltage	} for power loss calculation only		T _{VJ} = 175°C		0,95	V	
r _F	slope resistance					5	mΩ	
R _{thJC}	thermal resistance junction to case					0,45	K/W	
R _{thCH}	thermal resistance case to heatsink				0,15		K/W	
P _{tot}	total power dissipation	T _C = 25°C				330	W	
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; V _R = 0 V		T _{VJ} = 45°C		600	A	
C _J	junction capacitance	V _R = 400 V f = 1 MHz		T _{VJ} = 25°C	67		pF	
I _{RM}	max. reverse recovery current	I _F = 60 A; V _R = 300 V -di _F /dt = 200 A/μs		T _{VJ} = 25°C	8		A	
				T _{VJ} = 100°C	13		A	
t _{rr}	reverse recovery time			T _{VJ} = 25°C	35		ns	
				T _{VJ} = 100°C	110		ns	

Package TO-268AA (D3Pak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			70	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				5		g
F_C	mounting force with clip		20		120	N

¹⁾ I_{RMS} is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.

Product Marking



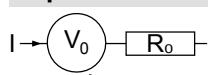
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEP60-06AT-TUB	DSEP60-06AT	Tube	30	509748

Similar Part	Package	Voltage class
DSEP60-06A	TO-247AD (2)	600
DHG60I600HA	TO-247AD (2)	600
DPH30IS600HI	ISOPLUS247 (2)	600

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 175^{\circ}\text{C}$



Fast Diode

$V_{0 \max}$ threshold voltage

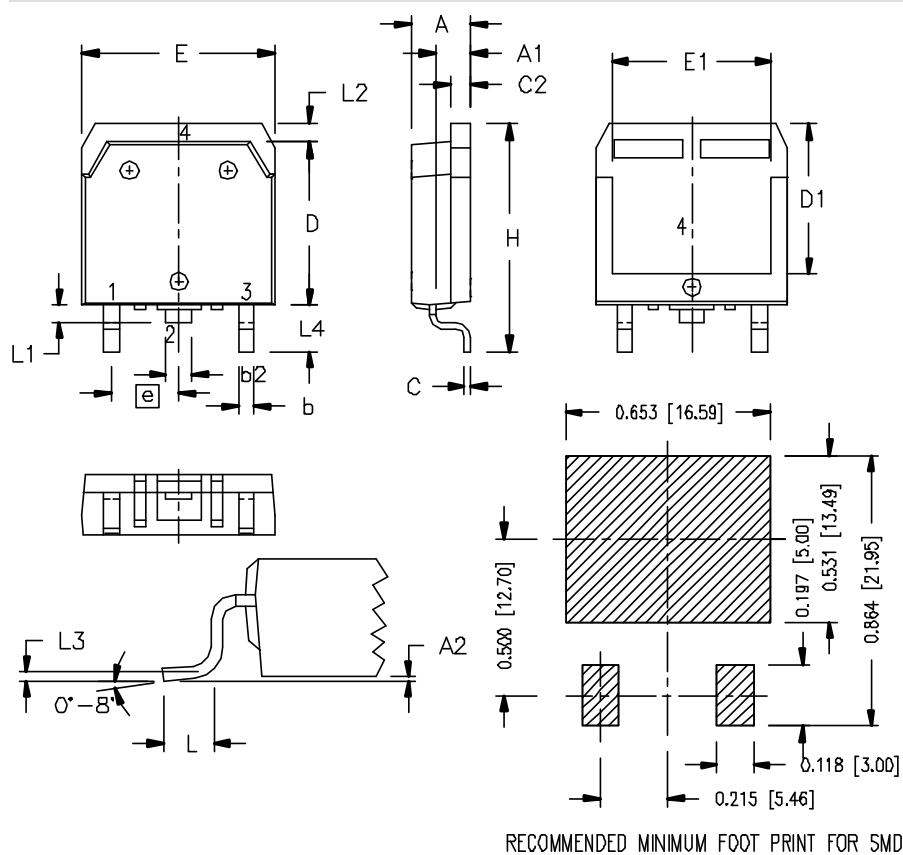
0,95

V

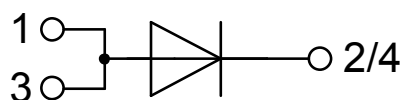
$R_{0 \max}$ slope resistance *

2,4

mΩ

Outlines TO-268AA (D3Pak)


Dim.	Millimeter		Inches	
	min	max	min	max
A	4.90	5.10	0.193	0.201
A1	2.70	2.90	0.106	0.114
A2	0.02	0.25	0.001	0.100
b	1.15	1.45	0.045	0.057
b2	1.90	2.10	0.075	0.083
C	0.40	0.65	0.016	0.026
C2	1.45	1.60	0.057	0.063
D	13.80	14.00	0.543	0.551
D1	12.40	12.70	0.488	0.500
E	15.85	16.05	0.624	0.632
E1	13.30	13.60	0.524	0.535
e	5.45 BSC		0.215 BSC	
H	18.70	19.10	0.736	0.752
L	2.40	2.70	0.094	0.106
L1	1.20	1.40	0.047	0.055
L2	1.00	1.15	0.039	0.045
L3	0.25 BSC		0.100 BSC	
L4	3.80	4.10	0.150	0.161



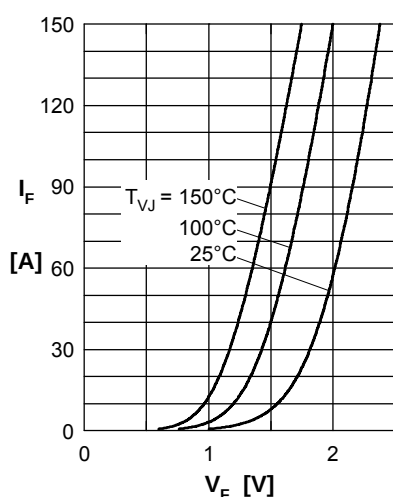
Fast Diode


Fig. 1 Forward current I_F versus V_F

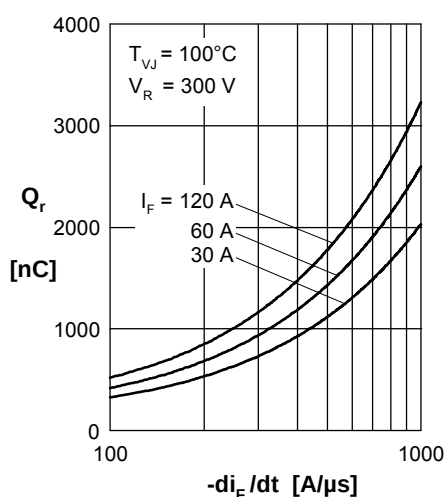


Fig. 2 Typ. reverse recovery charge Q_r versus $-di_F/dt$

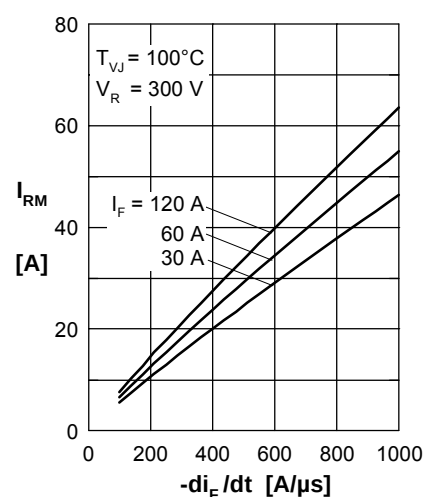


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

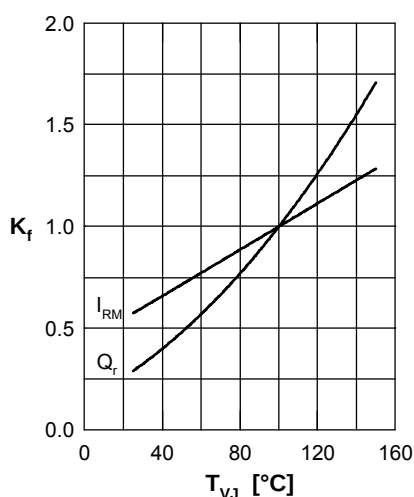


Fig. 4 Typ. dynamic parameters Q_r , I_{RM} versus T_{VJ}

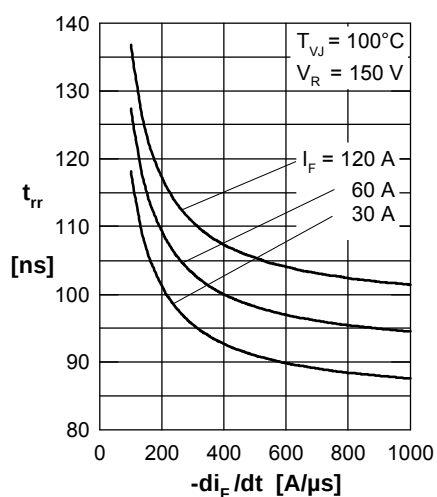


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

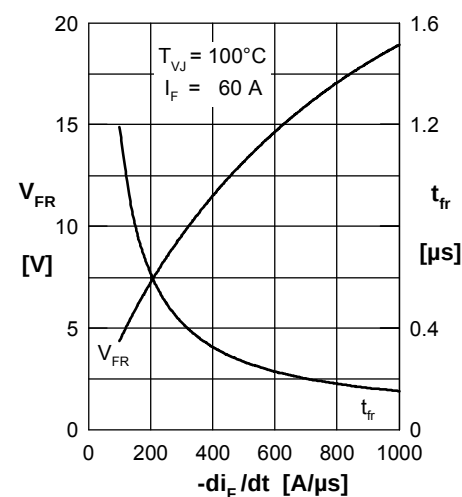


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

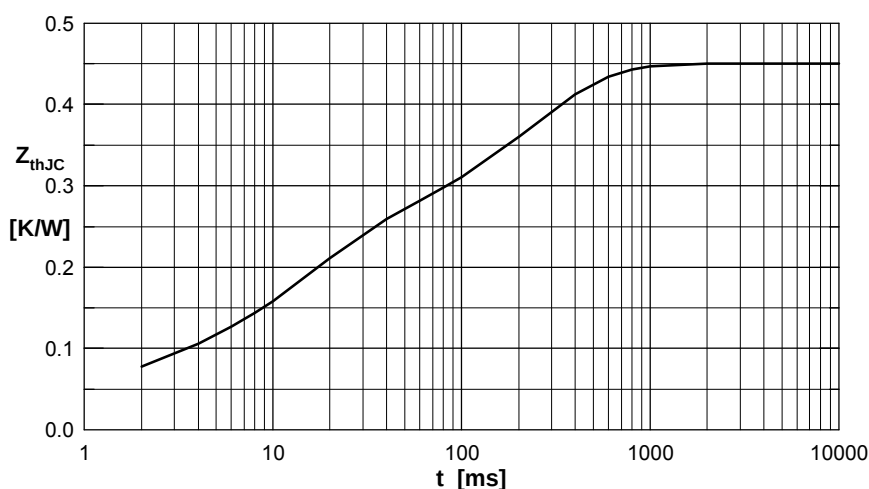


Fig. 7 Transient thermal resistance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0050	0.0001
2	0.0550	0.0010
3	0.1750	0.0140
4	0.2150	0.2300